PROCESS CP310

Small Signal Transistor

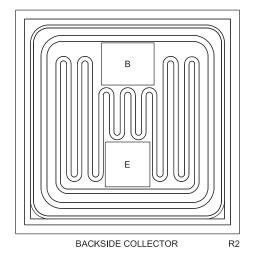
NPN - High Voltage Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	26 x 26 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	6.1 x 4.9 MILS
Emitter Bonding Pad Area	5.2 x 5.2 MILS
Top Side Metalization	AI - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

25,214

PRINCIPAL DEVICE TYPES

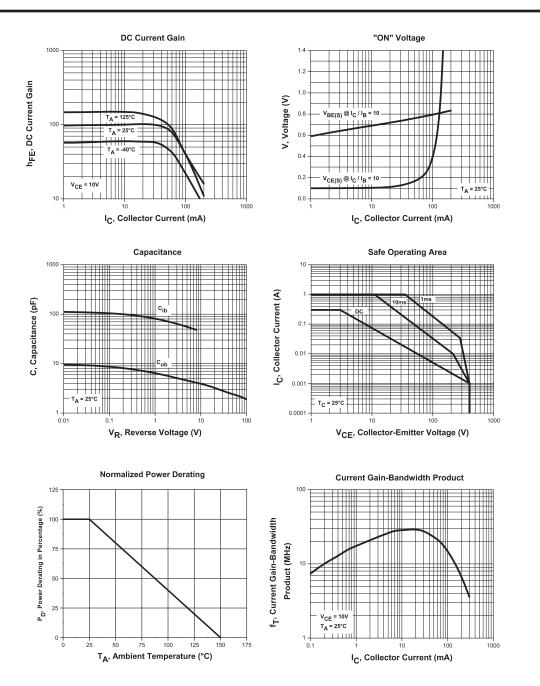
2N3439 2N3440 CMPTA42 CMPT6517 CXTA44 CZTA42 CZTA44 MPSA42 MPSA44

R4 (22-March 2010)

PROCESS CP310

Typical Electrical Characteristics





R4 (22-March 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- · Special wafer diffusions
- · PbSn plating options
- Package details
- · Application notes
- · Application and design sample kits
- · Custom product and package development

CONTACT US

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